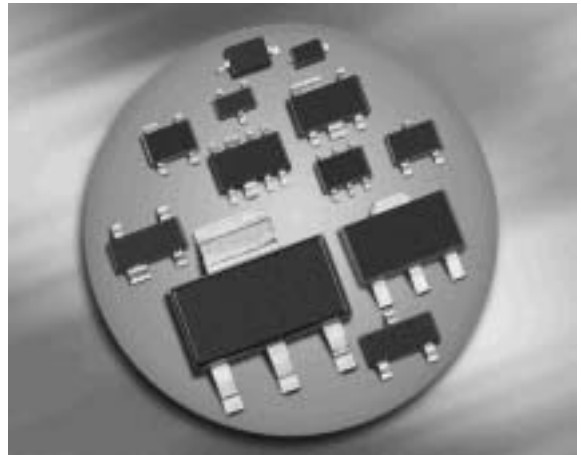
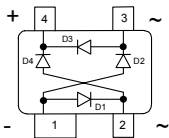


Low VF Schottky Diode Array

- Reverse voltage: 30 V
- Forward current: 0.9 A
- Small diode quad array for polarity independence, reverse polarity protection and low loss bridge rectification
- Very low forward voltage:
0.5 V typ. @ 0.7 A (per diode)
- Fast switching
- Pb-free (ROHS compliant) package¹⁾
- Qualified according AEC Q101



BAS3007A-RPP



Type	Package	Configuration	Marking
BAS3007A-RPP	SOT143	bridge	E1s

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage ²⁾	V_R	30	V
Peak reverse voltage ²⁾	V_{RM}	30	
RMS reverse voltage ²⁾	$V_{R(RMS)}$	21	
Forward current ²⁾	I_F		mA
$T_S \leq 46^\circ\text{C}$		900	
$T_S \leq 82^\circ\text{C}$		700	
Non-repetitive peak surge forward current ($t \leq 10$ ms)	I_{FSM}	5	A
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

¹Pb-containing package may be available upon special request

²For $T_A > 25^\circ\text{C}$ the derating of V_R and I_F has to be considered. Please refer to the attached curves.

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 95	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Reverse current (per diode) ²⁾	I_R				μA
$V_R = 12\text{ V}$		-	-	30	
$V_R = 30\text{ V}$		-	-	350	
Forward voltage (per diode) ²⁾³⁾	V_F				V
$I_F = 100\text{ mA}$		-	0.35	0.4	
$I_F = 350\text{ mA}$		-	0.4	0.5	
$I_F = 500\text{ mA}$		-	0.45	0.55	
$I_F = 700\text{ mA}$		-	0.5	0.6	
$I_F = 900\text{ mA}$		-	0.6	0.7	

AC Characteristics

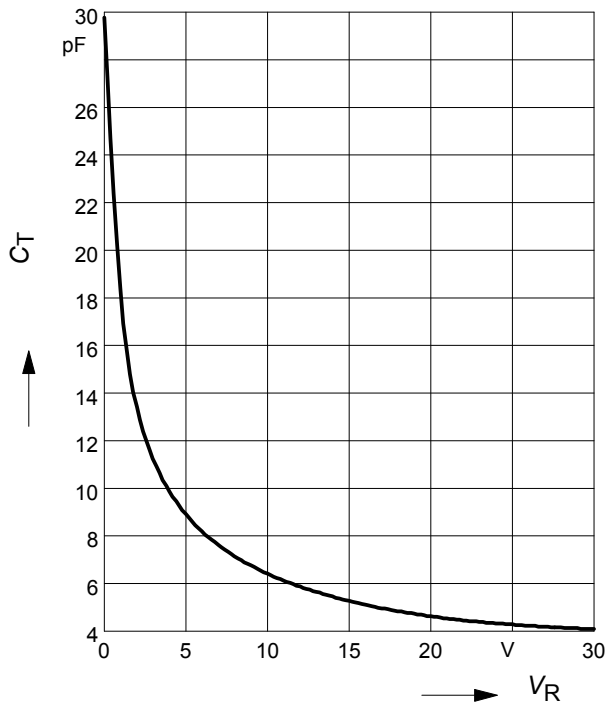
Diode capacitance (per diode)	C_T	-	9	15	pF
$V_R = 5\text{ V}$, $f = 1\text{ MHz}$					

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

²⁾Pulsed test, $t_p = 300\text{ }\mu\text{s}$; $D = 0.01$
³⁾When used as shown for Reverse Polarity Protection (RPP, see page 4), the voltage available to the circuit being protected will be two diode drops below the power supply voltage. In other words, the supply current will pass through two diodes.

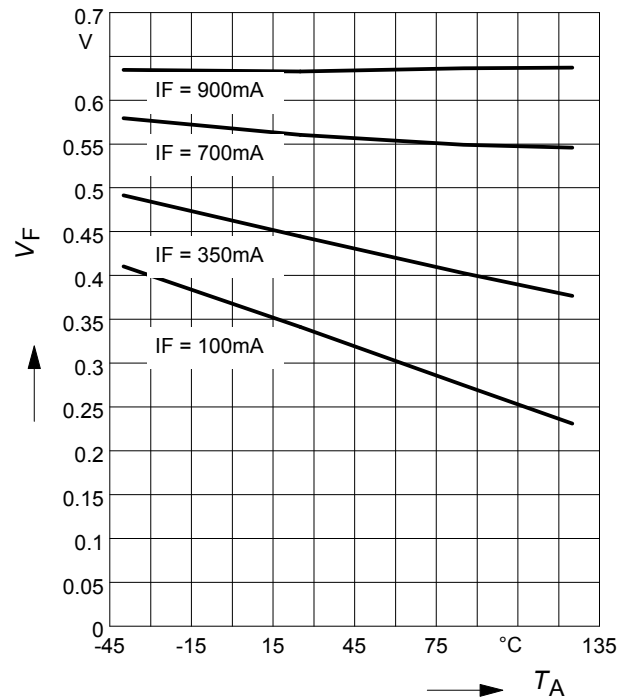
Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$ (per diode)



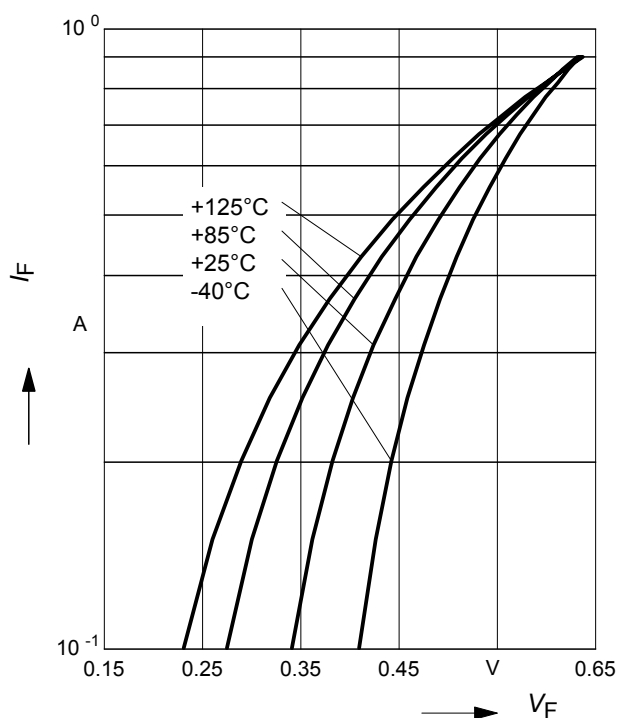
Forward Voltage $V_F = f(T_A)$

$I_F = \text{Parameter}$ (per diode)



Forward current $I_F = f(V_F)$

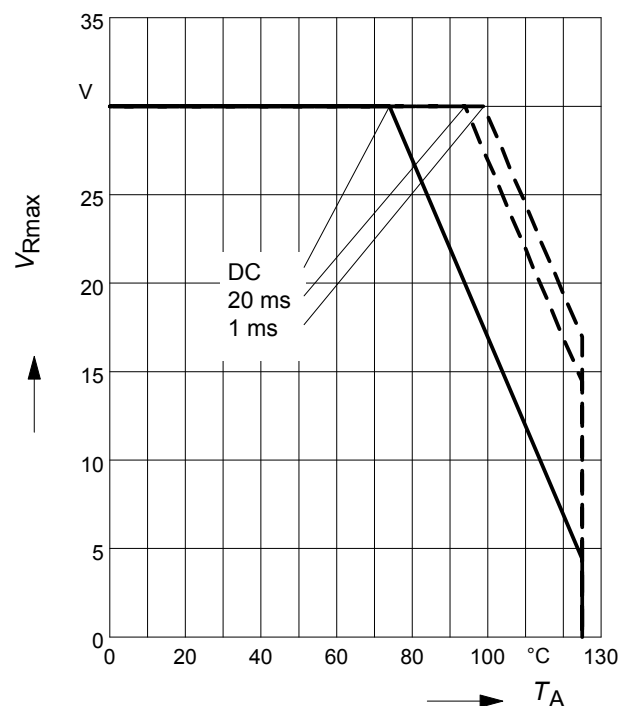
$T_A = \text{Parameter}$ (per diode)



Permissible Reverse voltage $V_R = f(T_A)$

$t_p = \text{Parameter}$, Duty cycle < 0.01

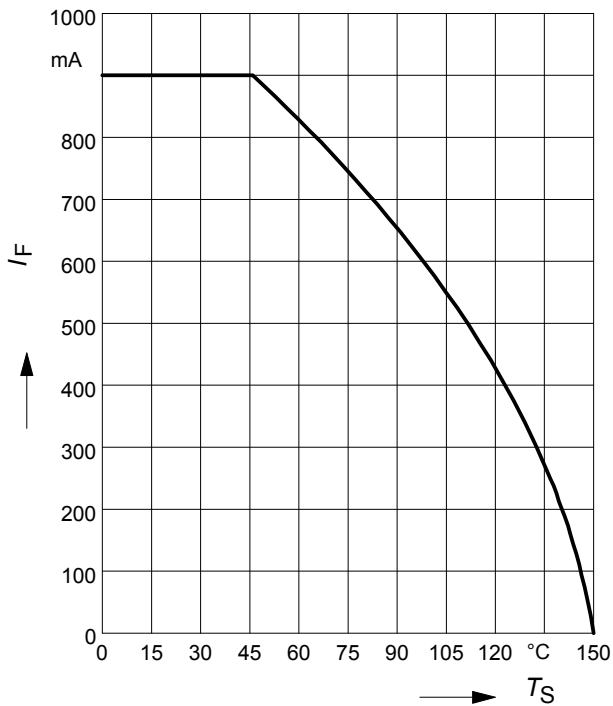
Device mounted on PCB with $R_{th} = 160\text{ K/W}$



Forward current $I_F = f(T_S)$

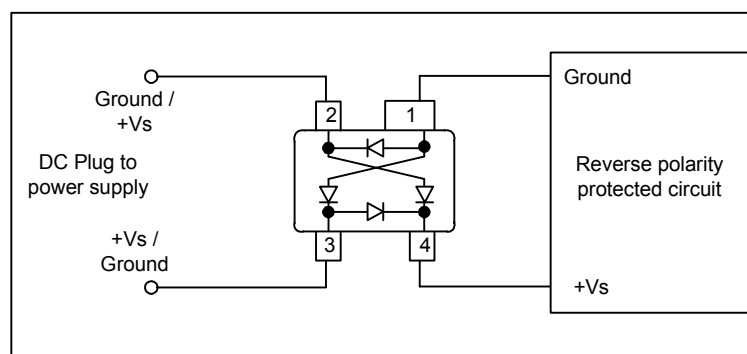
Current flows through two chips

per package at the same time (per array)



Application example BAS3007A-RPP

Advanced Reverse Polarity Protection(RPP): due to diode orientation, circuit at the right will be protected from damage and will also function normally in the event reverse polarity is applied to pins 2 and 3 of the BAS3007A-RPP.



Technical drawing of a 4-pin connector. The drawing includes a perspective view of the component and two orthographic views (top and side) with detailed dimensions and tolerances.

Dimensions and Tolerances:

- Top View:**
 - Overall width: 2.9 ± 0.1
 - Pin spacing (between pins 1 and 2): 1.9
 - Pin diameter: 0.2
 - Pin length (from base): $0.8^{+0.1}_{-0.05}$
 - Pin 1 diameter: $0.4^{+0.1}_{-0.05}$
 - Pin 2 diameter: 0.25 M B
 - Pin 3 diameter: 0.2 M A
 - Pin 4 diameter: 0.2 M A
- Side View:**
 - Overall height: 1.3 ± 0.1
 - Pin 1 height: 1 ± 0.1
 - Pin 2 height: 0.1 MAX.
 - Pin 3 height: $0.08 \dots 0.15$
 - Pin 4 height: $0 \dots 8^\circ$
 - Pin 1 angle: 10° MAX.
 - Pin 2 angle: 10° MAX.
 - Pin 3 angle: 10° MAX.
 - Pin 4 angle: $0 \dots 8^\circ$
 - Pin 1 length: 2.4 ± 0.15
 - Pin 2 length: 0.15 MIN.
 - Pin 3 length: 0.15 MIN.
 - Pin 4 length: 0.15 MIN.

Diagram illustrating the marking on the BFP181 package:

- Manufacturer:** infineon
- Date code (YM):** 2005, June
- Pin 1:** Indicated by a line pointing to the first pin.
- Type code:** BFP181

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